

TOSHIBA TRANSISTOR TOSHIBA (DISCRETE/OPTO) ————
SILICON PNP EPITAXIAL TYPE (PCT PROCESS)**2SA968B**

T 33-19

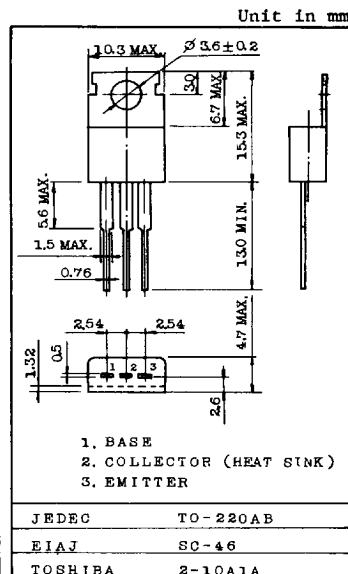
POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

- High Transition Frequency: $f_T=100\text{MHz}$ (Typ.)
- Complementary to 2SC2238B

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	2SA968B V_{CB0}	-200	V
Collector-Emitter Voltage	2SA968B V_{CE0}	-200	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-1.5	A
Emitter Current	I_E	1.5	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)	P_C	25	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Mounting Kit No. AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB}=-160\text{V}$, $I_E=0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=-5\text{V}$, $I_C=0$	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	2SA968B $V_{(BR)CE0}$	$I_C=-10\text{mA}$, $I_B=0$	-200	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EB0}$	$I_E=-1\text{mA}$, $I_C=0$	-5	-	-	V
DC Current Gain	h_{FE} (Note)	$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}$, $I_B=-50\text{mA}$	-	-	-1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-5\text{V}$, $I_C=-500\text{mA}$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE}=-10\text{V}$, $I_C=-100\text{mA}$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$	-	30	-	pF

Note: h_{FE} Classification O: 70~140, Y: 120~240

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2SA968B

